

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (Original) An interconnect structure, comprising:
a substrate;
a first metal line disposed on the substrate;
a first insulating layer disposed on the substrate, covering the first metal line;
a second metal line disposed on the first insulating layer;
a second insulating layer covering the second metal line;
ITO (indium tin oxide) wiring electrically connecting the first and second metal lines; and
a passivation structure disposed on the second insulating layer with an opening therein to expose and enclose the ITO wiring.
2. (Original) The interconnect structure as claimed in claim 1, wherein the substrate is a TFT-array substrate for a flat display panel.
3. (Original) The interconnect structure as claimed in claim 1, wherein the first and second metal lines, the ITO wiring and the passivation structure are disposed in a non-display area of the TFT-array substrate.
4. (Original) The interconnect structure as claimed in claim 3, wherein the first metal line is a gate metal line formed simultaneously with gate metal lines in a display area of the TFT-array substrate.

5. (Original) The interconnect structure as claimed in claim 3, wherein the second metal line is a source/drain metal line that is formed simultaneously with source/drain metal lines on a display area of the TFT-array substrate.

6. (Original) The interconnect structure as claimed in claim 1, wherein the ITO wiring comprises a first ITO electrode disposed in the first and second insulating layers in contact with the first metal line, a second ITO electrode disposed in the second insulating layer in contact with the second metal line, and an ITO layer connecting the first and second ITO electrodes.

7. (Original) The interconnect structure as claimed in claim 1, wherein the thickness of the passivation structure is between 3 and 4 μ m.

8. (Original) The interconnect structure as claimed in claim 1, wherein the opening in the passivation structure is rectangular.

9. – 13. Canceled.